XN0F256

Silicon NPN epitaxial planar type

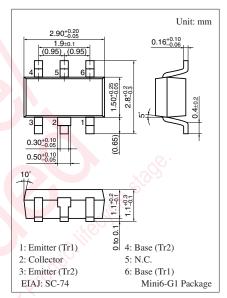
For muting

■ Features

- Two elements incorporated into one package (Collector-coupled transistors with built-in resistor)
- \bullet Low collector-emitter saturation voltage $V_{\text{CE}(\text{sat})}$
- Reduction of the mounting area and assembly cost by one half

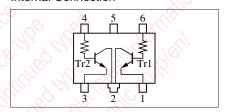
■ Absolute Maximum Ratings $T_a = 25$ °C

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|------------------|-------------|------|
| Collector-base voltage (Emitter open) | V_{CBO} | 30 | V |
| Collector-emitter voltage (Base open) | V _{CEO} | 20 | V |
| Emitter-base voltage (Collector open) | V _{EBO} | 5 | V |
| Collector current | I_{C} | 600 | mA |
| Total power dissipation | P_{T} | 300 | mW |
| Junction temperature | T_{j} | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |



Marking Symbol: 6A

Internal Connection



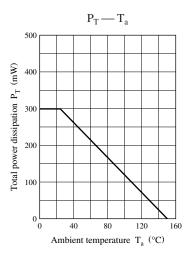
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

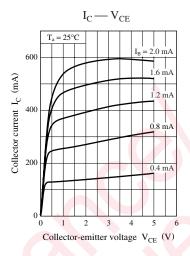
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|--|------|-----|------|------|
| Collector-base voltage (Emitter open) | V _{CBO} | $I_C = 1 \mu A, I_E = 0$ | 30 | | | V |
| Collector-emitter voltage (Base open) | V _{CEO} | $I_C = 1 \text{ mA}, I_B = 0$ | 20 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 1 \mu A, I_C = 0$ | 5 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 30 \text{ V}, I_E = 0$ | | | 1 | μΑ |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = 5 \text{ V}, I_C = 0$ | | | 1 | μΑ |
| Forward current transfer ratio | h_{FE} | $V_{CE} = 5 \text{ V}, I_{C} = 50 \text{ mA}$ | 100 | | 600 | _ |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = 50 \text{ mA}, I_B = 2.5 \text{ mA}$ | | | 80 | mV |
| Input resistance | R_1 | | -30% | 4.7 | +30% | kΩ |
| Transition frequency | f_T | $V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$ | | 200 | | MHz |

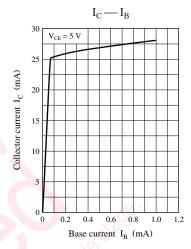
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

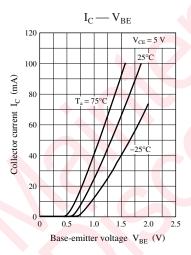
Publication date: July 2003 SJJ00120BED 1

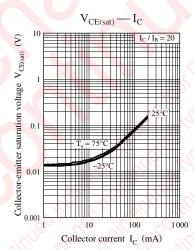
Panasonic

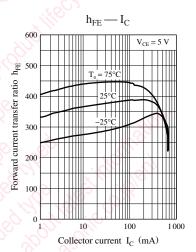












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